

## **AWARD WINNING PERFORMANCE**

High performance devices call for high performance test and burn-in solutions and require participation by the entire test ecosystem including contactors, sockets, the DUT board, along with the environment that testing takes place in and the methodology applied. This session provides insight to each step beginning with the development of a statistical model to identify the optimized bandwidth for spring probes. Next up is a look at environmental factors that can readily impact socket performance and thus indirectly test yield. The third presentation verifies test methodology to troubleshoot a device that is having issues in a very high performance test contactor to determine the cause of the issues and affect changes to prevent them from reoccurring. Lastly, we'll hear about the unique challenges to create an optimized test methodology for 25 to 40 GHz RF amplifiers, mixers, and down converters in LFCSP (QFN) and WLCSP packages, considering connectivity issues between DUT board and sockets.

### **Design of Experiments Using Spring Probe Parameters for Optimized Socket Bandwidth**

Mike Fedde, Ila Pal—Ironwood Electronics, Inc.



This Paper

### **Socket Performance vs. Environmental Conditions**

Gert Hohenwarter—GateWave Northern, Inc.

### **Troubleshooting Test Oscillation Problems**

Jeff Sherry—Johnstech International Corporation

### **Optimization of Package, Socket and PC Board for 25 to 40GHz RF Devices**

Carol McCuen, Phil Warwick—R&D Circuits, Inc.

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# Socket Performance vs. Environmental Conditions

**Gert Hohenwarter**  
**GateWave Northern, Inc.**



2013 BiTS Workshop  
March 3 - 6, 2013



## Background

- DC Socket performance expected to change with 'external contributions'
- RF performance changes can range from imperceptible to very noticeable

## Objective

- Demonstrate impact of condensation and ice formation
- Examine contributions from metal build-up

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Socket Performance vs. Environmental Conditions

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## Approach

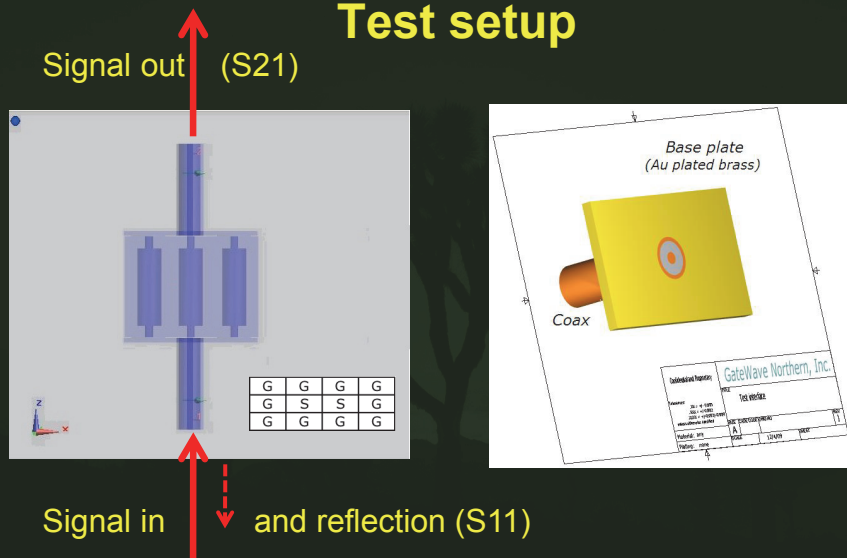
- Set up test environment as used in standard RF characterization, record performance
- Introduce 'contaminants' and record changes
- Corroborate findings via 3D finite element analysis

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## Test setup



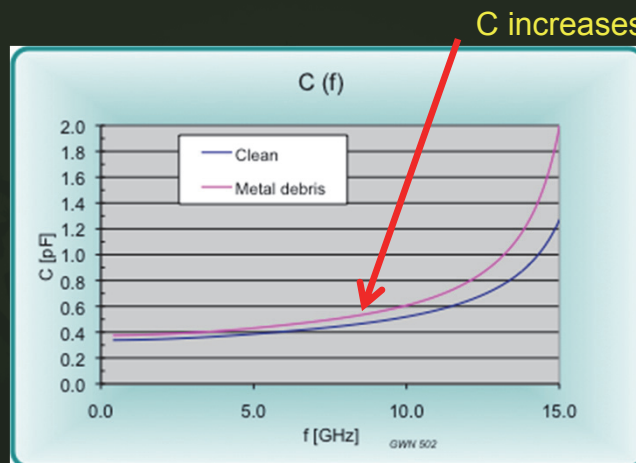
Setup reflects typical RF characterization environment

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## Contaminant: Metal – Capacitance



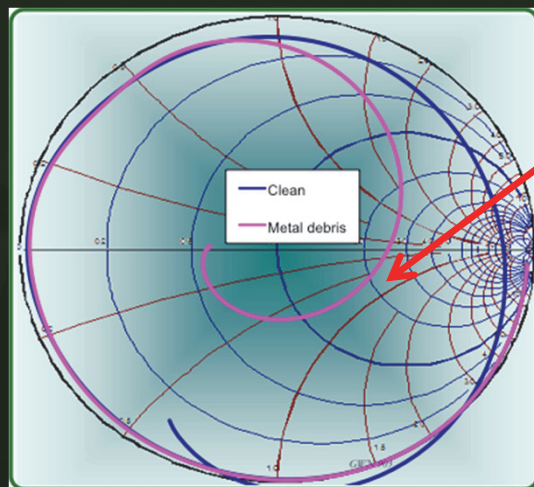
Capacitance  $C$  to ground before and after contamination

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## Contaminant: Metal – Smith chart



Loss increases at elevated frequencies

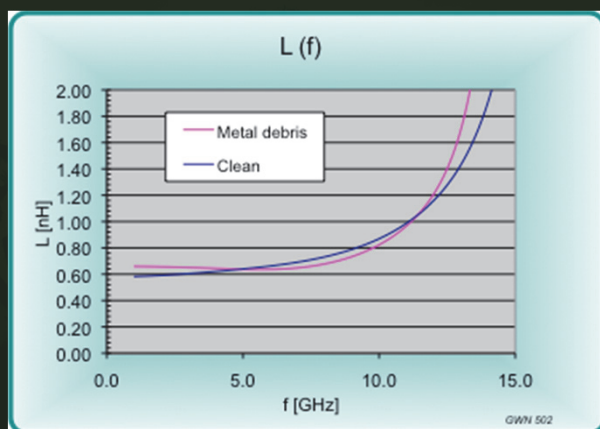
Open circuit S11 before and after contamination

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## Contaminant: Metal – Inductance



L -> ?

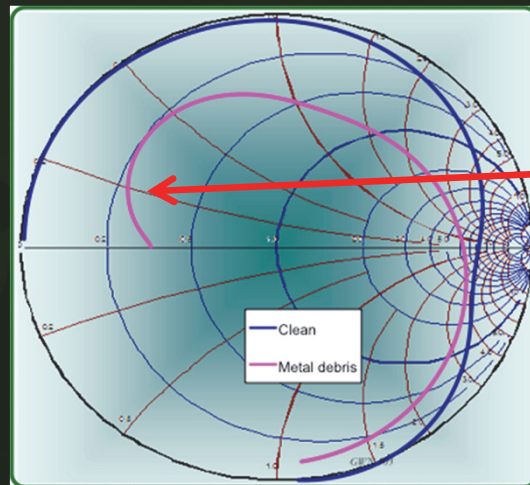
Loop inductance before and after contamination

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## Contaminant: Metal – Smith chart



Resistance  
increases  
at DC and  
low  
frequencies

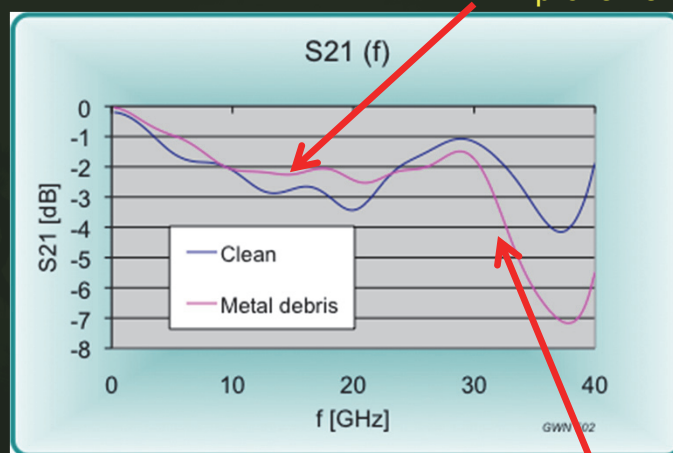
Short circuit S11 before and after contamination

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## Contaminant: Metal – S21



Improvement

Deterioration

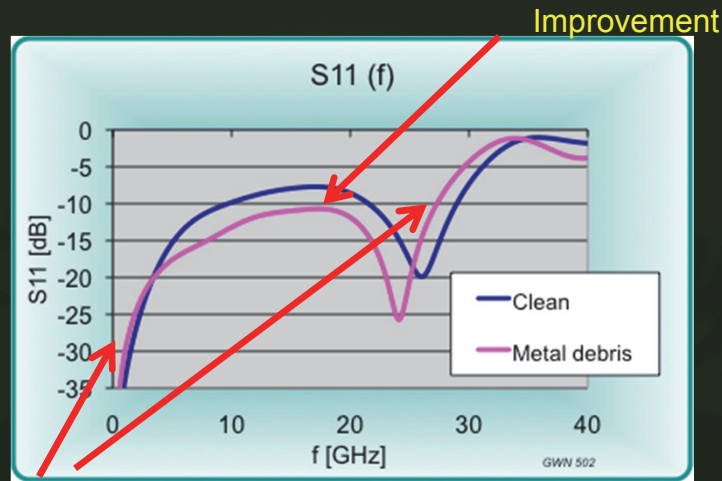
S21 insertion loss before and after contamination

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## Contaminant: Metal – S11



Deterioration

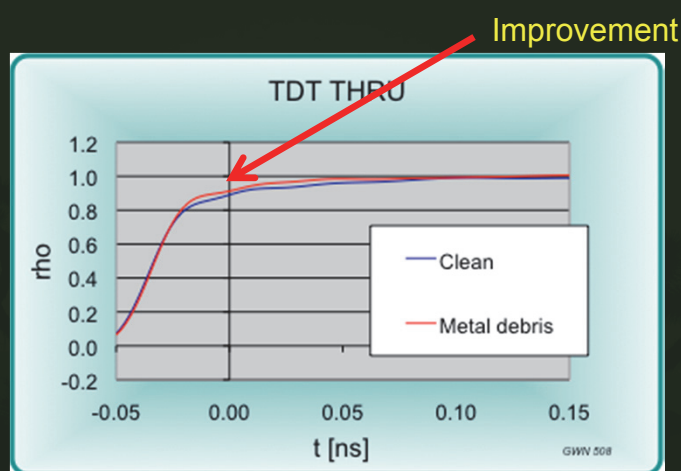
S11 return loss before and after contamination

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## Contaminant: Metal - TDT



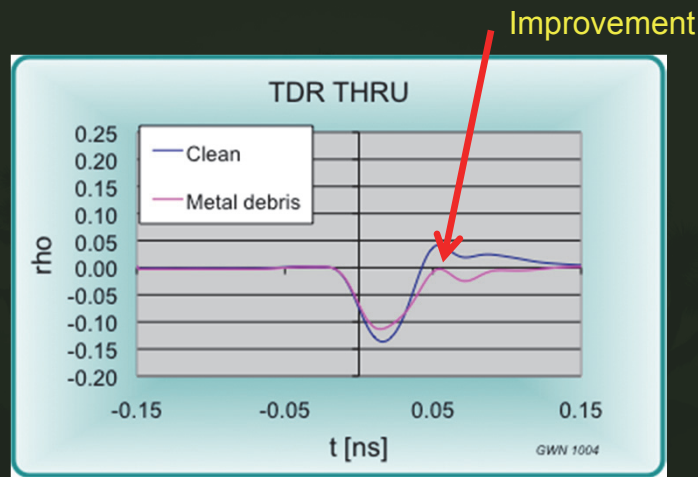
Time domain transmission trace before and after contamination

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## Contaminant: Metal - TDR



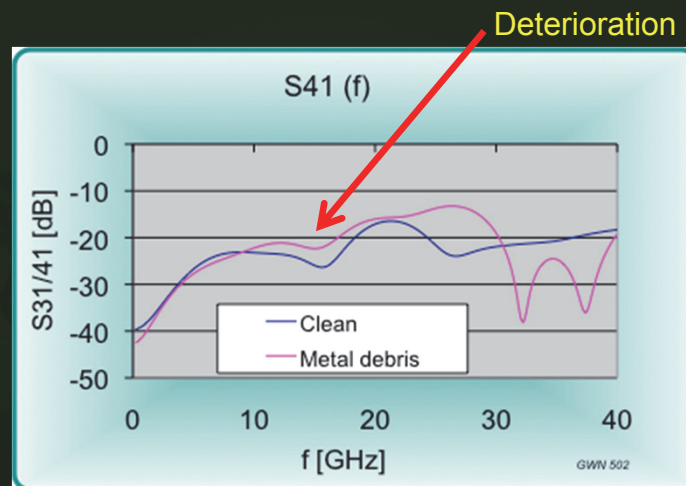
Time domain reflectometer trace before and after contamination

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## Contaminant: Metal – S41 (FEXT)



S41 far-end crosstalk before and after contamination

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## Contaminant: Metal - Comments

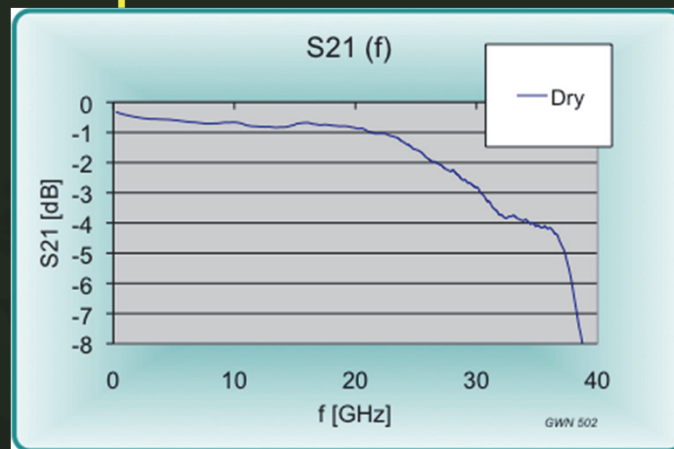
- In this case metal build-up results in a performance improvement at low frequencies and a deterioration at elevated frequencies
- Results are specific to a particular socket and test environment
- Low frequency increases in resistance did interfere with inductance characterization

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## Impact of moisture: S21



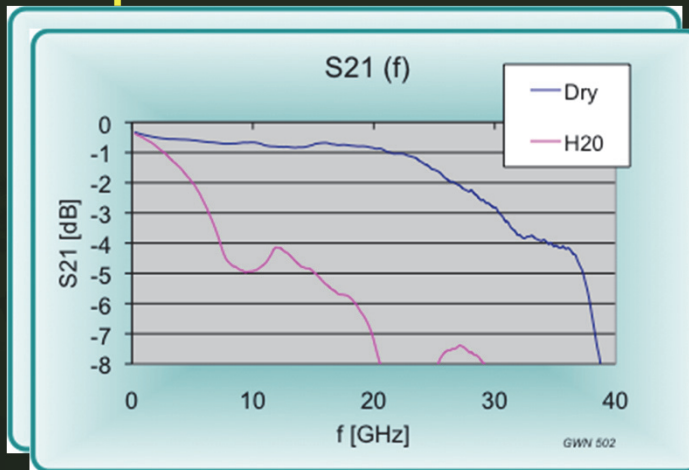
### S21 insertion loss before and after condensation

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## Impact of moisture: S21



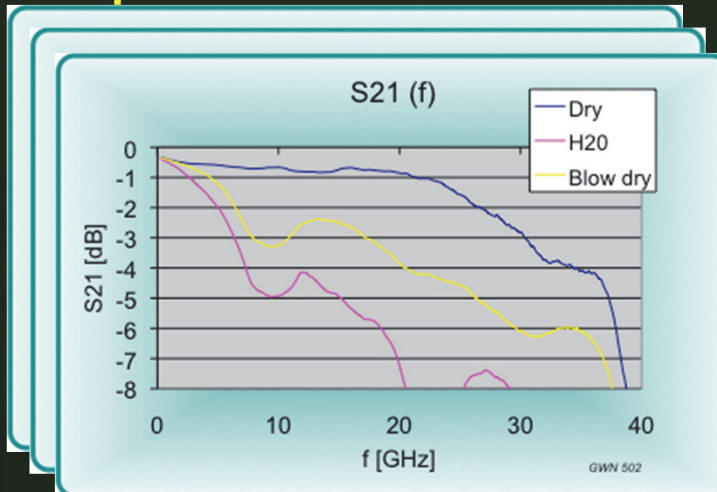
### S21 insertion loss before and after condensation

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## Impact of moisture: S21



-1 dB: 21.3 2.6 4.2 GHz

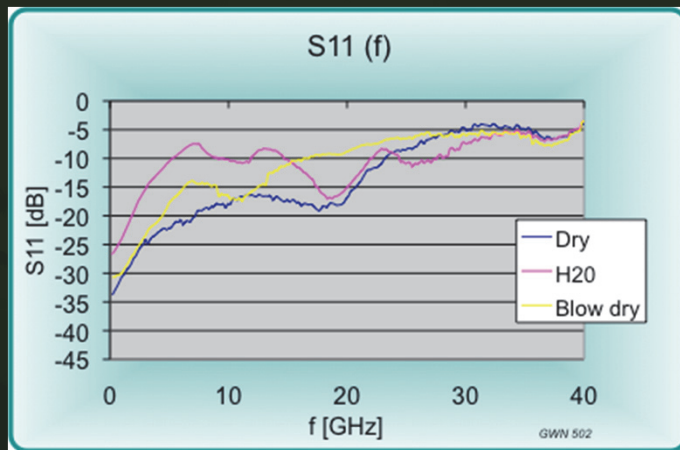
### S21 insertion loss before and after condensation

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## Impact of moisture: S11



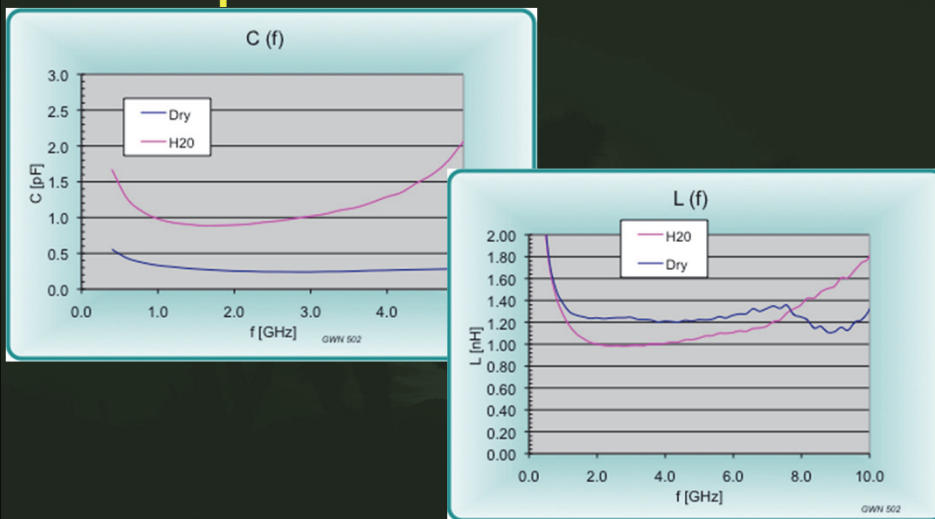
S11 return loss before and after condensation

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## Impact of moisture: C and L



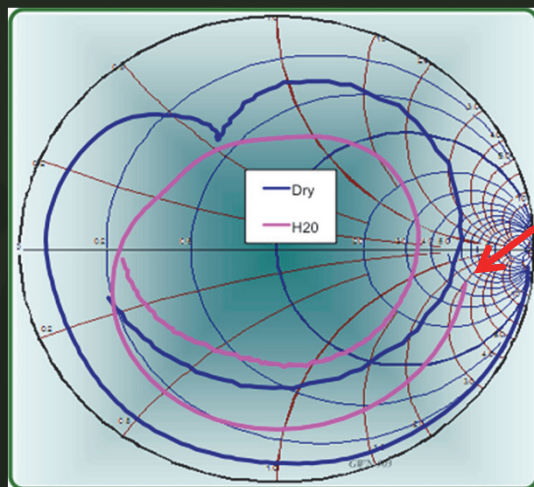
Capacitance and inductance before and after condensation

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## Impact of moisture: Smith chart



Significant loss at low frequencies means also increased leakage at DC

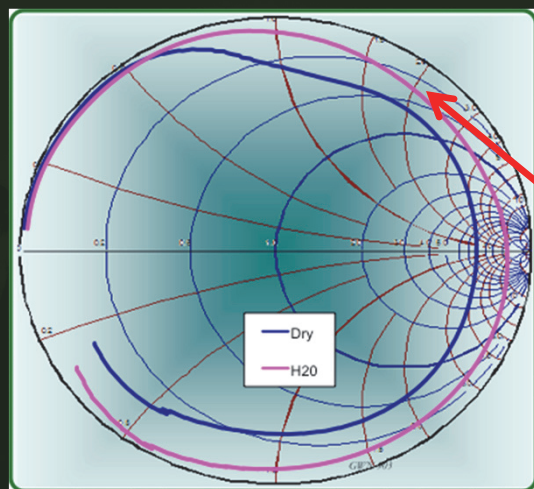
Open circuit S11 before and after moisture exposure

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## Impact of moisture: Smith chart



Less loss at elevated frequencies for short circuit condition

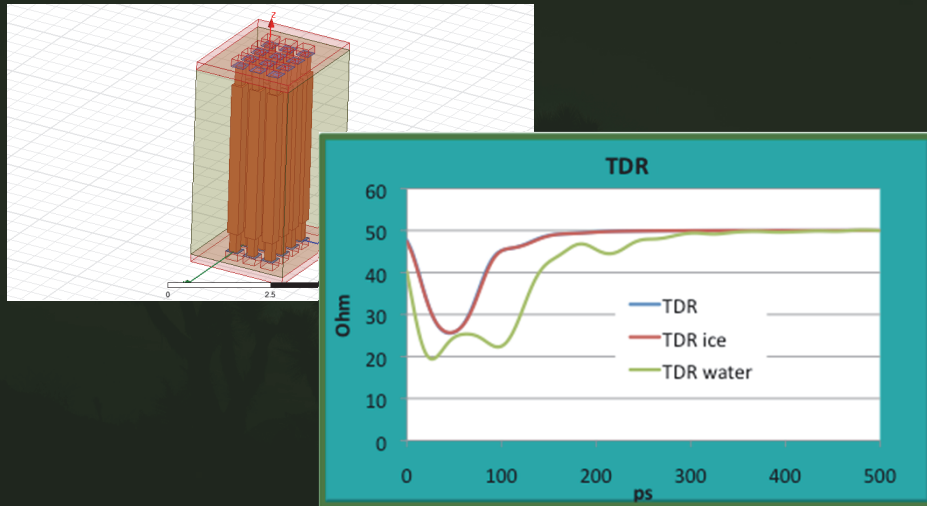
Short circuit S11 before and after condensation

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## HFSS Model: TDR



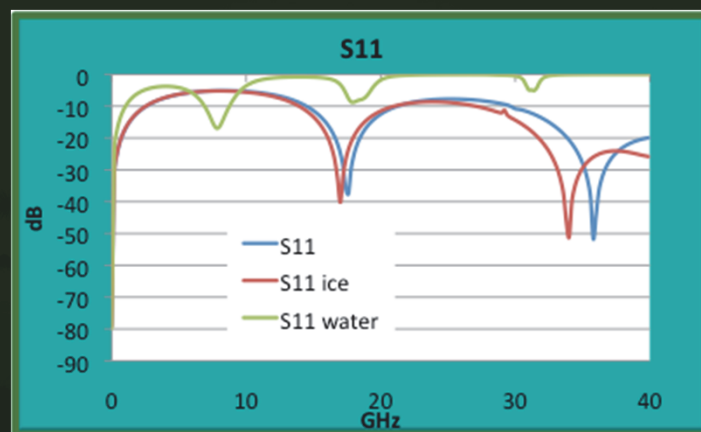
TD reflection before and after condensation

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## HFSS Model: Return loss



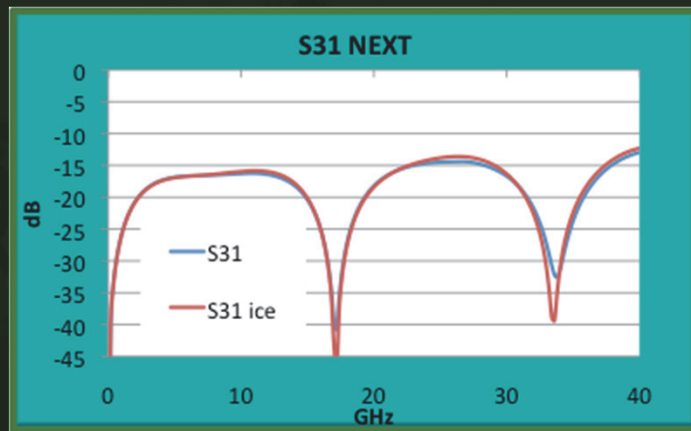
Return loss before and after condensation

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## HFSS Model: Crosstalk



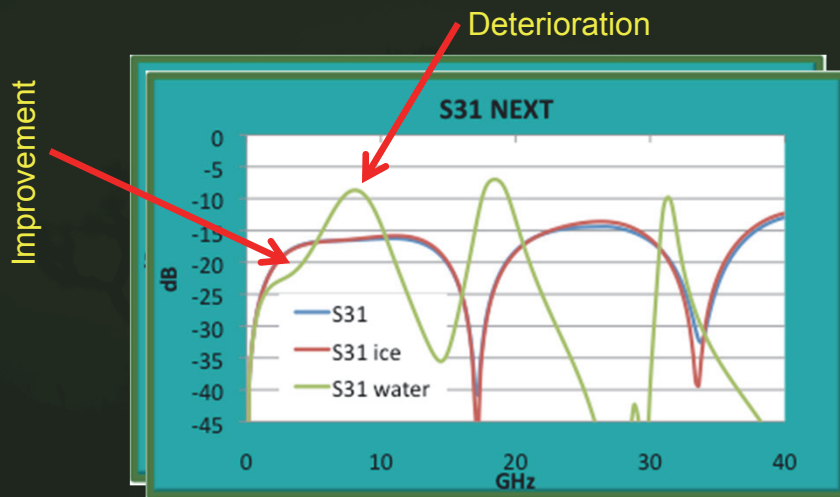
**NEXT crosstalk before and after condensation**

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## HFSS Model: Crosstalk



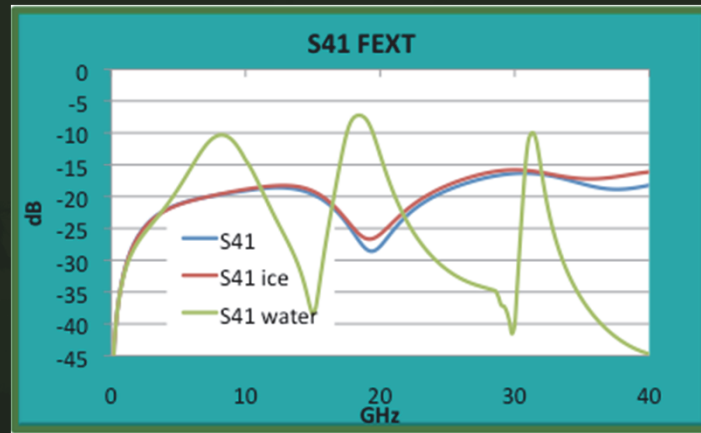
**NEXT crosstalk before and after condensation**

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## HFSS Model: Crosstalk



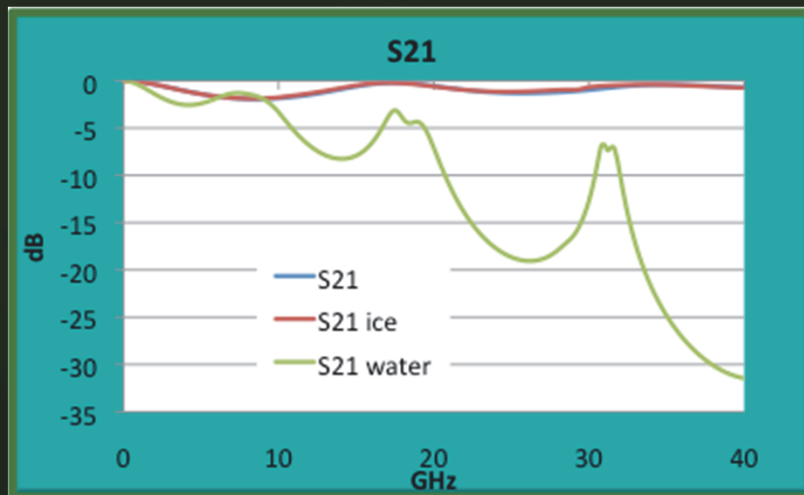
FEXT crosstalk before and after condensation

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## HFSS Model: Insertion loss



Insertion loss S21 before and after condensation

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## Conclusion

- Even small amounts of moisture can severely reduce socket RF performance
- Metal buildup can have noticeable effect on RF performance, but impact is not guaranteed to be negative.
- Experimental performance changes can be predicted by 3D FEA model
- Contamination and condensation do not always result in performance deterioration.

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